Bulletin I0132J 05/99

International
IOR Rectifier

IR180DG..HCB SERIES

HIGH POWER RECTIFIER DIODES

- **Junction Size:** **Square 180 mils**
- **Wafer Size:** **4"**
- **V_{RRM} Class:** **600 and 1200 V**
- **Passivation Process:** **Glassivated MESA**
- **Reference IR Packaged Part:** **26MB Series**

Major Ratings and Characteristics

Parameters	Units	Test Conditions
V_{FM} Maximum Forward Voltage	1030 mV	T_J = 25°C I_F = 25A
V_{RRM} Reverse Breakdown Voltage Range	600 and 1200 V	T_J = 25°C I_R = 100µA **(1)**

(1) Nitrogen flow on die edge.

Mechanical Characteristics

Nominal Back Metal Composition, Thickness	Cr - Ni - Ag (1 KA - 4 KA - 6 KA)
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Chip Dimensions	180 x 180 mils (see drawing)
Wafer Diameter	100 mm, with std. < 110 > flat
Wafer Thickness	300 µm
Maximum Width of Sawing Line	130 µm
Reject Ink Dot Size	0.25 mm diameter minimum
Ink Dot Location	See drawing
Recommended Storage Environment	Storage in original container, in dessicated nitrogen, with no contamination

Ordering Information Table

Device Code

IR	180	D	G	12	H	CB
1	2	3	4	5	6	7

1 - International Rectifier Device

2 - Chip Dimension in Mils

3 - Type of Device: D = Standard Recovery Diode

4 - Passivation Process: G = Glassivated MESA

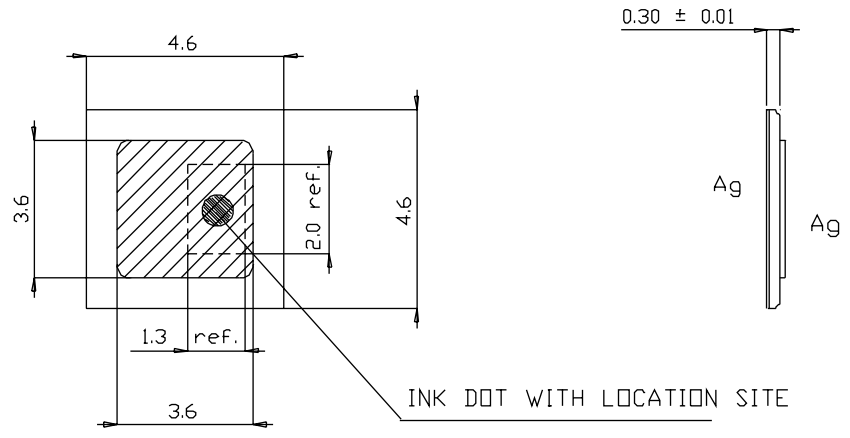
5 - Voltage code: Code x 100 = V_{RRM}

Available Class
06 = 600V
12 = 1200V

6 - Metallization: H = Silver (Anode) - Silver (Cathode)

7 - Probed Uncut Die

Outline Table

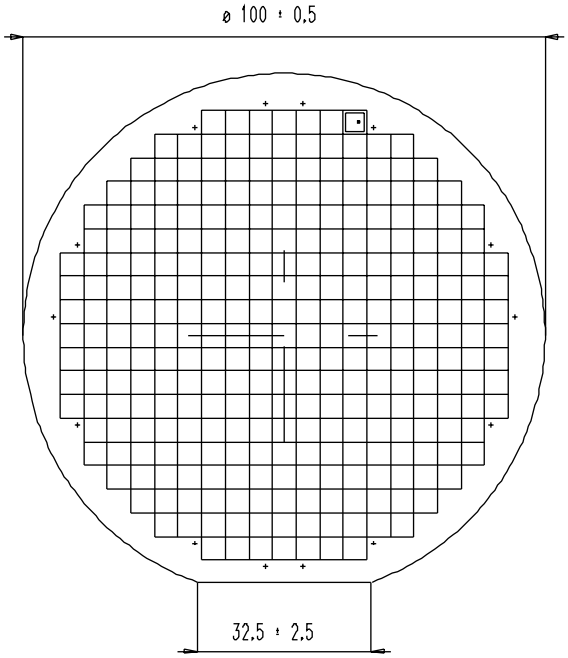


All dimensions are in millimeters

Wafer Layout

TOP VIEW

N° 293 Basic Cells



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